Pinholes and their effects of APV25 chips

Pinholes

- sensor strips are capacitively coupled to APV25
- The capacitors, integrated on the sensor strips, can occasionally have a short circuit→ pinhole.
- Pinhole can give DC current into/out from APV, which can:
 - 1. permanently disable the whole APV chip on p-side
 - due to APV INVERTER, used to change signal polarity and increase the dynamic range only on p-side (APV dynamic range +7MIPs /-2.5MIPs)
 - problem only arises on p-side (INVERTER) if current flow INTO APV:
 - APV input sits at +0.75V w.r.t APV_GND=HV_Bias
 - p side strips, collect holes, sit at HV_Bias+Ileak*Rbias →cna inject current INTO APV
 - problem only if Ileak is big (rad damaged sensors) or/and several pinholes are connected to the same chip (details in backup slides)
 - 2. disable the single APV channel where pinhole is connected.
 - same effect on p and n side
- In CMS (single side sensor, p-side strips) all pinholes were then NOT connected to the APV chip to avoid problem 1

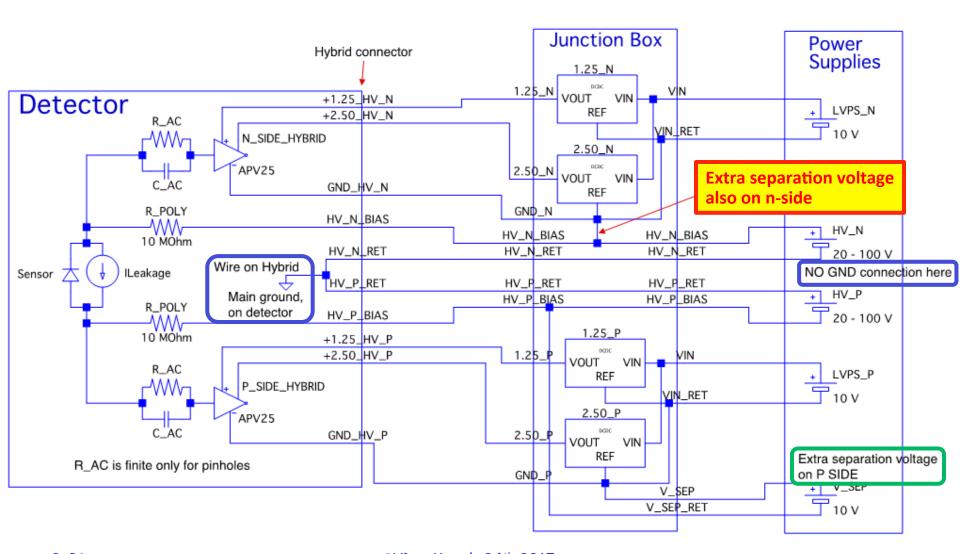
What we do in Belle2-SVD for pinholes

- In Belle2-SVD we proposed a new strategy for the pinholes!
- Saturation effect of the whole p-side chip can be avoided applying an extra voltage (Vsep) on APV_GND w.r.t HV_Bias
 - can rise Vsep to positive voltage so the current flows out of the APV chip, to sensor strip, and saturation cannot happpen.
 - Extra voltage used already in BaBar to inhibit issues due to pinholes/p-stop short
- Advantages: disconnecting all the pinholes (as in CMS) can be difficult & new pinholes can develop later (radiation accidents!)
- This scheme (next slide) was proposed originally only to p side, since chip saturation cannot happen on n-side
 - CAEN boards for p side foreseen
- Recent studies on APVDAQ teststand (with real SVD modules) proved Vsep is effective:
 - 1. to avoid whole chip saturation on p side (expected)
 - 2. to cure single pinholes on p and n side (new)
 - 3. to recover single noisy strips: field plate effect of AC metal connected to the Vsep voltage via APV input (new)

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CAEN board for n side are needed

New Powering Scheme

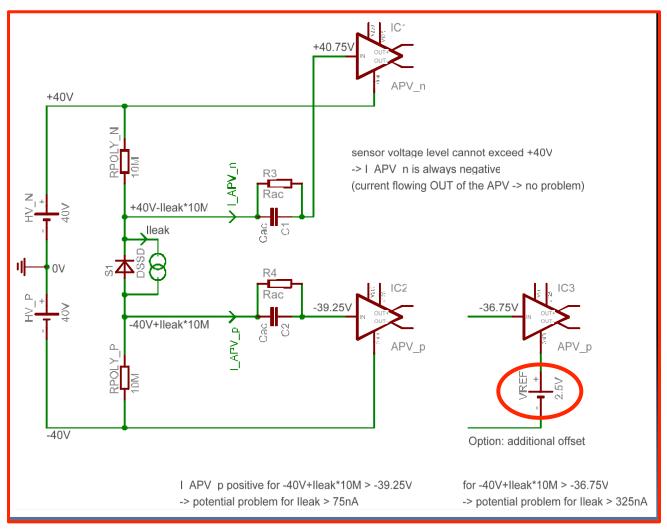


Vsep-extravoltage advantages

Recent studies on teststand with real SVD modules proved Vsep effects and various advantages on p and n side

- 1. Saturation effect on p side, on chips with several pinholes connected, demonstrated and cured with Vsep
 - Whole chip saturation starts with Vsep<-3V
 - All chans including pinholes, work normally -2.5V<Vsep<-0.5V
 - Pinholes stop working with Vsep>-0.5 V the other chans ok
- 2. Vsep can cure single connected pinholes on p & n side
 - with Vsep set to equalize the strip voltage and the input of the APV (+0.75V) no significant DC current is flowing in the pinhole and APV channel can work normally: Vsep=-0.75V cure pinhole, for very low Ileak
- 3. Applying Vsep, via the APV input, on AC metal strips (no pinholes/AC capacitor OK) can be beneficial for noisy strips:
 - AC metal acts as a field plate above the n+ strip implant
 - With the right polarity/value can reduce strip leakage current coming from defects localized at the Si/Si02 surface
 - Noise reduction on defective strips observed/effect still under study

Pinholes studied on APVDAQ teststand



- p-side only: large
 current flow INTO
 APV, (several
 pinholes) is a
 problem for the
 whole chip
- p & n side: small current (single pinhole) disable a single APV channel
- Remedy: offset voltage between HV bias and APV_GND
- Some noisy channels (not pinholes) can be recovered with Vsep acting on AC metal as field plate

APV response to internal calibration

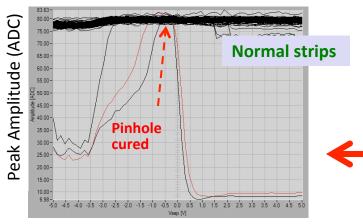
Signal (MIP equivalent) injected from internal APV calibration circuit

- Peak amplitude:
 - 85 ADC for normal strips
 - smaller for pinholes connected

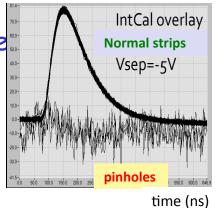
Peak amplitude on pinholes reacts to Vsep extra voltage, as expected

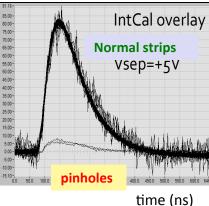
Vsep negative, -0.75V can cure single: pinholes

equalize strip voltage and APV input

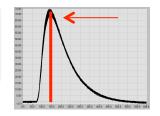


Normal strips IntCal overlay **APV #1** output Vsep=oV pinholes time (ns)



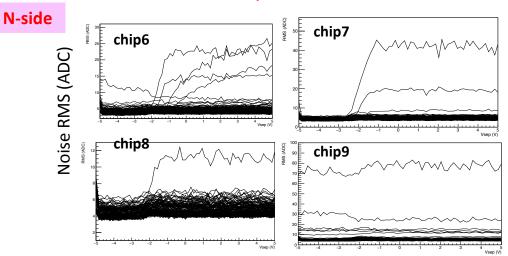


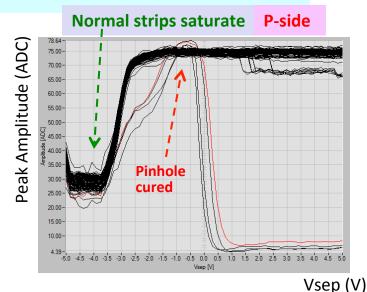
Only peak amplitude sampled & fine Vsep scan implemented on APVDAQ

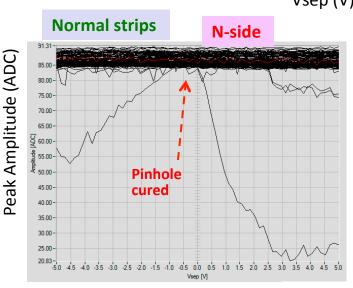


Vsep scan results

- Whole chip saturation induced artificially with Vsep<-3V in chips with several pinholes connected
- 2. Single pinholes on p and n side cured
- 3. Some single strips noisy (not pinhole) can be cured: field plate effect of AC metal connected to the Vsep voltage via APV input (new effect under study)
- Vsep adds some degree of freedom on p and n side to compensate some defects







Vsep (V)

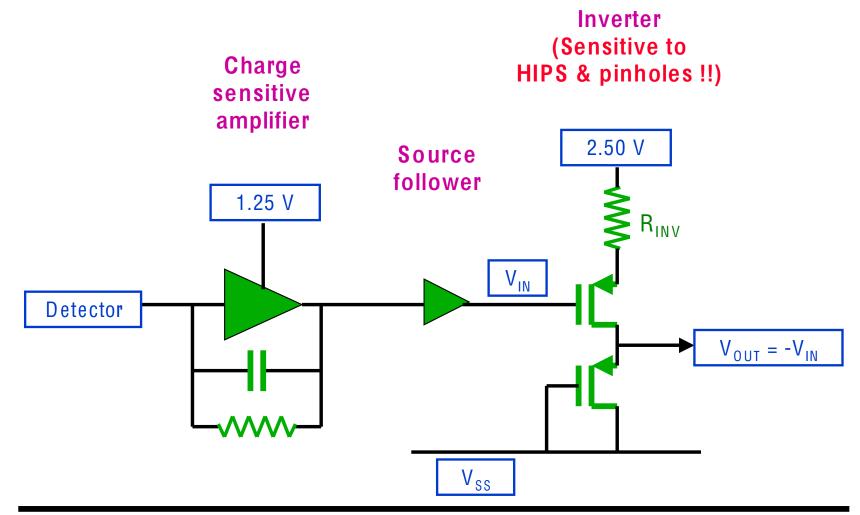
G. Rizzo

Backup



Introduction Internal Workings of the APV





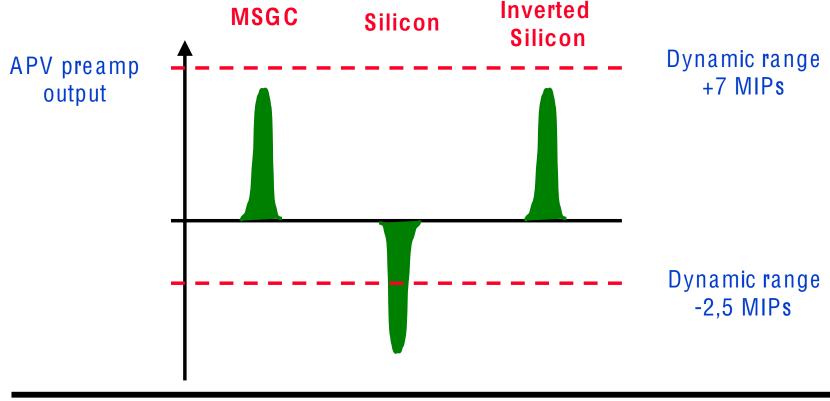


Introduction Internal Workings of the APV



Why is the inverter there?

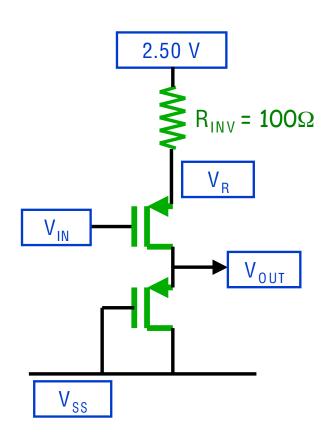
It increases APV dynamic range for silicon strip detector.





Introduction How HIPs & Pinholes affect the APV





❖ Big signal from silicon (holes) gives -ve pulse at V_{IN}:

- ➤Inverter FET switches hard on, which steals current from 127 other inverters.

 (APV disabled until capacitor discharges.)
- ➤ N.B. If R_{INV} were reduced, total current available to inverters would increase.

❖Leakage current via pinhole into APV:

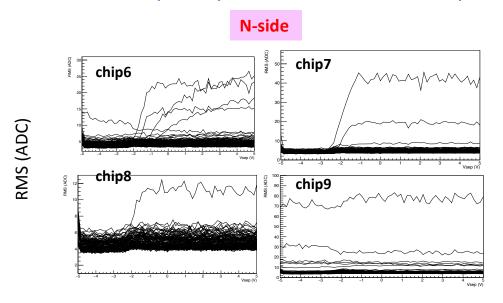
>Same again, but permanent.

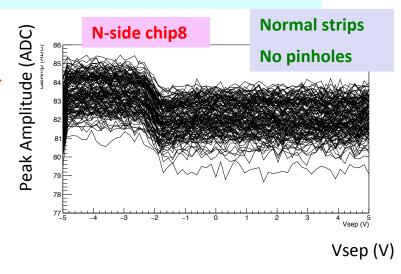
❖Leakage current via pinhole out of APV :

➤Inverter FET switches hard off. Takes no current, so other 127 channels still work.

Vsep scan on n side HPK sensor

- Some single strips become very noisy @ Vsep>-2V → Vsep<-2V can cure them!
- Other noisy strip not sensitive to Vsep





- Only seen on 1 HPK sensor
- Seen also on other sensor in HEPHY?

- Possible explanation for both effect:
 - field plate effect of AC metal connected to the Vsep voltage via APV input

Vsep scan on n side HPK sensor

- 1. Small reduction of Calamp (and increase in caltmax) on all n side strip @ Vsep>-2V
- 2. Some single strips become very noisy @ Vsep>-2V
- Possible explanation for both effects:
 - field plate effect of AC metal connected to the Vsep voltage via APV input
 - Negative voltage (Vsep<-2V) on AC n side metal reduces the extension of the electrons accumulation layer and reduces the effective width of n+ implant
 - 1. C interstrip, proportional to width /pitch, is reduced for all strips and consequently Calamp (increase) and Caltmax move (sensitive to the Capacitance connected to the APV input)
 - 2. When the extension of the n strip implant changes the localized defects at surface that can produce leakage current can/cannot contribute to the strip leakage current and noise increase/decrease.
- Field effect on AC metal could be studied on sensors (n and p side) and, to be pragmatic, effects on modules noise vs Vsep should be studied.
- We might find the best optimization for Vsep operation on n and p side to: cure pinholes, reduce the noisy strips

Vsep (V)

Vsep scan and field effect on AC metal

- With Vsep negative the AC metal acts as a field plate and reduces the accumulation layer estension close to the n+ strip implant > effective implant width w_n+ is reduced
- Interstrip capacitance, proportional to width/pitch, is reduced → Peak amplitude increases slightly
- The Electric field close to the n+ strip is modified by the field plate effect
 - Some defects very close to the surface Si-SiO2 (that can be the origin of high leakage current) can stop to contribute to the strip leakage current??
 - The peak electric field can be lowered, thus reducing the impact ionization in spots where localized defects are responsible for high field values.

